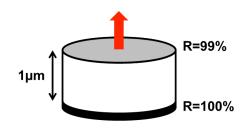
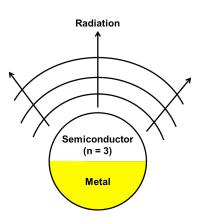
## HW #1 Due Feb. 25 (Thursday) in class

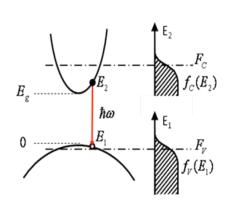
1. Consider a vertical cavity surface-emitting laser with a top mirror reflectivity of 99% and a bottom mirror reflectivity of 100%, an effective cavity length of 1μm, and a diameter of 2 μm. The confinement factor is 100%. The residue loss of the active media is 10cm<sup>-1</sup> and the refractive index is 3.5. The laser wavelength is 1 μm.



- a. Find the quality factor (Q) of the cavity.
- b. Find the threshold gain and quantum efficiency of the laser.
- 2. Consider a laser with metallodielectric cavity shown on the right. It consists of a 100-nm-diameter spherical cavity with half metal and half semiconductor. Assume 30% of the energy is in the metal, and the remaining 70% is in the semiconductor. The quality factor of the metal is 50 (note: the Q of a material describes the loss of that material, it is different from the cavity Q). Assume the residue loss in semiconductor is negligible (i.e., its material Q is  $\infty$ ). The cavity acts like a dipole antenna and radiates optical energy (i.e., output light). Assume the radiation Q is 500 (i.e., the Q associated with the radiation loss is 500). The laser wavelength is 1  $\mu$ m.



- a. What is the total Q of the cavity?
- b. What is the threshold gain and quantum efficiency of the laser?
- 3. Refer to the diagram on the right. Under biased condition, both conduction and valence bands are populated. The electron distribution in conduction band is described by Fermi-Dirac distribution, f<sub>C</sub>(E<sub>2</sub>), with quasi-Fermi energy F<sub>C</sub>. The electron distribution in valence band is described by Fermi-Dirac distribution, f<sub>V</sub>(E<sub>1</sub>), with quasi-Fermi energy F<sub>V</sub>. Here, E<sub>1</sub> and E<sub>2</sub> are related by an optical transition (i.e., they have the same k). The optical matrix element is



$$\left| \hat{e} \cdot \overrightarrow{P}_{cv} \right|^2 = \frac{m_0}{6} E_p$$
 with  $E_p = 25.7 \text{ eV}$ 

- a. Use the energy reference below (i.e,  $E_V = 0$  and  $E_C = E_g$ , the bandgap energy), find  $E_1$  and  $E_2$  as functions of the photon energy,  $h\omega$ .
- b. Derive  $f_c(E_2(h\omega))$  as a function of  $h\omega$ .
- c. Derive  $f_V(E_1(h\omega))$  as a function of  $h\omega$ .

- d. Assuming  $E_g = 1 \text{ eV}$ ,  $F_C F_V = 1.2 \text{ eV}$ ,  $m_e^* = 0.1 m_0$ ,  $m_h^* = 0.4 m_0$ . Calculate and plot the emission probability  $f_e(h\omega) = f_C(E_2(h\omega)) \cdot \left[1 f_V(E_1(h\omega))\right]$  for photon energies from 0.8 to 1.5 eV. Plot for two temperatures: T = 0 and T = 300 K.
- e. Repeat part d) for the Fermi inversion factor:  $f_g(h\omega) = f_C(E_2(h\omega)) f_V(E_1(h\omega))$
- f. Plot the gain spectra for T = 0 and T = 300 K for the condition given in d).
- g. Plot the spontaneous emission spectra for T = 0 and T = 300 K for the condition given in d).

